

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of) Art Unit: Unassigned
Hideomi SUZAWA et al.) Examiner: Unassigned
Serial No. 10/086,628)
Filed: March 4, 2002)
For: SEMICONDUCTOR DEVICE AND)
MANUFACTURING METHOD)
THEREOF)

CERTIFICATE OF MAILING

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Washington, D.C. 20231, on 2/7/02

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 7 and 11-12 as follows:

7. (Amended) A semiconductor device according to claims 1 to 5 wherein a side face of one of the source region and the drain is aligned with one of the source wiring and the electrode.

11. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 or 9 wherein in the eighth step, a part of the first amorphous semiconductor film and the conductive film and the second amorphous semiconductor film are etched with a chlorine type gas.


12. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 or 9 wherein the chlorine type gas is selected from Cl_2 and BCl_3 , HCl and SiCl_4 or a gas containing a plurality of gases from these gases.

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REMARKS

Applicants have amended claims 7 and 11-12 to correct the dependency.
Examination on the merits is respectfully requested.

Respectfully submitted,



Eric J. Robinson
Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 7 and 11-12 as follows:

7. (Amended) A semiconductor device according to claims 1 to [6] 5 wherein a side face of one of the source region and the drain is aligned with one of the source wiring and the electrode.

11. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 [to 10] or 9 wherein in the eighth step, a part of the first amorphous semiconductor film and the conductive film and the second amorphous semiconductor film are etched with a chlorine type gas.

12. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 [to 11] or 9 wherein the chlorine type gas is selected from Cl_2 and BCl_3 , HCl and SiCl_4 or a gas containing a plurality of gases from these gases.

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